

# Dimiter Alexandrov

## List of Publications by Year in descending order

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17  
papers

89  
citations

1684188  
5  
h-index

1720034  
7  
g-index

17  
all docs

17  
docs citations

17  
times ranked

92  
citing authors

#	ARTICLE	IF	CITATIONS
1	Low energy nuclear fusion reactions in solids: Experiments. International Journal of Energy Research, 2021, 45, 12234-12246.	4.5	1
2	Low temperature growth of InAlN on epitaxially grown SiC/Si (111) wafers. , 2017, , .		0
3	Low temperature epitaxial deposition of GaN on LTCC substrates. , 2017, , .		1
4	Modeling of metal-oxide-semiconductor capacitor on Indium Gallium Nitride 1- channel model. , 2012, , .		0
5	InN grown by migration enhanced afterglow (MEAgrow). Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 41-44.	1.8	15
6	Dependence of the magnetic properties of MnGaN epitaxial layers on external electrical field. Open Chemistry, 2009, 7, 175-178.	1.9	0
7	Impedance Study of GaN and InGaN Semiconductor Anion Selective Electrodes. Electroanalysis, 2008, 20, 789-796.	2.9	7
8	INTERACTION BETWEEN POSITIVE HYDROGEN IONS AND ELECTRONS LOCATED IN INDIUM NITRIDE CONTAINING OXYGEN IMPURITIES. Nano, 2008, 03, 387-390.	1.0	0
9	Electron Band Structure of MnGaN. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
10	Structure of Isolated Oxygen Impurity States in InN. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
11	Evaluation of GaN and In <sub>0.2</sub> Ga <sub>0.8</sub> N Semiconductors as Potentiometric Anion Selective Electrodes. Electroanalysis, 2007, 19, 1799-1806.	2.9	4
12	Dielectric susceptibility of InN and related alloys. Journal of Materials Science: Materials in Electronics, 2007, 18, 123-126.	2.2	0
13	Energy band gap and optical properties of non-stoichiometric InN theory and experiment. Journal of Crystal Growth, 2006, 288, 261-267.	1.5	5
14	Energy band gaps of InN containing oxygen and of the In <sub>x</sub> Al <sub>1-x</sub> N interface layer formed during InN film growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 954.	2.1	12
15	Absorption and photoluminescence features caused by defects in InN. Journal of Crystal Growth, 2004, 269, 77-86.	1.5	29
16	Excitons of the Structure in Zinc-Blende In <sub>x</sub> Ga <sub>1-x</sub> N and their Properties. Materials Research Society Symposia Proceedings, 2002, 743, L11.11.1.	0.1	0
17	Excitons of the structure in wurtzite In <sub>x</sub> Ga <sub>1-x</sub> N and their properties. Journal of Crystal Growth, 2002, 246, 325-340.	1.5	15